

WHAT IS CLAIM IS:

32. Memory device comprising:

- a. a resistive layer with a plurality of solid electrolyte elements and a metallic layer, or
- b. a lamination of said resistive layer, said metallic layer and a conductive layer.

33. The device of claim **32** wherein said resistive layer is a layer with a plurality of solid electrolyte elements embedded in an insulator layer.

34. The device of claim **33** wherein the size of solid electrolyte elements is in the range of about 1.0-50 nm.